

AMENDMENTS TO THE CLAIMS:

Kindly cancel claim 3, without prejudice, and amend claims 1 and 2, as shown below.

This listing of claims will replace all prior versions and listings of claims in the
Application:

Claim 1 (currently amended): An on-wafer monitoring system capable of measuring an
operation of a plasma treatment apparatus on a wafer, said system comprising:

one or a plurality of sensor sections, a power source unit, and an I/O unit that
inputs/outputs signals from/to outside, which are provided on a silicon substrate,

wherein each of said sensor sections has a pattern portion which is a plasma treatment
target, [[and]] under said pattern portion, a plurality of electrodes and insulating films for
separating ions and electrons of plasma by energy, and an uppermost electrode of said
electrodes has the same potential as that of said silicon substrate,

and said pattern portion, said plurality of electrodes and insulating films have pores for
sensing.

wherein said power source unit takes out power from plasma potential or takes out
power from photoelectromotive force of a PLZT device.

Claim 2 (currently amended): The on-wafer monitoring system according to Claim 1,

wherein a plurality of electrodes of said sensor sections are Al electrodes, and [[space]]
insulating films between each of the Al electrodes ~~is insulated by~~ are γ -Al₂O₃.

Claims 3-4 (cancelled)

Claim 5 (previously presented): The on-wafer monitoring system according to Claim 3,

wherein said I/O unit inputs/outputs signals from/to outside by light.

Claim 6 (previously presented): The on-wafer monitoring system according to Claim 1,

wherein said system includes an ion energy analyzer, which has a collector electrode at a sensor section bottom and measures ion current in the collector electrode to obtain ion energy distribution, as said sensor.

Claim 7 (previously presented): The on-wafer monitoring system according to Claim 1,

wherein said system includes a photon detector, which detects light made incident into a pattern by photoinduced current generated in an insulating film, as said sensor.

Claim 8 (previously presented): The on-wafer monitoring system according to Claim 1,

wherein said photon detector forms a metal thin film on said insulating film, and detects light having energy equivalent to or more than an energy difference between the work function of the metal and the conduction band bottom of said insulating film out of light transmitted from the metal thin film.

Claim 9 (previously presented): The on-wafer monitoring system according to Claim 1,

wherein said system includes a photon detector that detects light by a photo diode, as said sensor.

Claim 10 (previously presented): The on-wafer monitoring system according to Claim 1,

wherein said system includes an ion radical analyzer, which identifies radicals and ions by detecting light emission by the collision between electrons from an electron gun and radicals or ions, as said sensor.

Claim 11 (original): The on-wafer monitoring system according to Claim 10,

wherein said ion radical analyzer has a spectroscope for detecting light emission.

Claim 12 (previously presented): The on-wafer monitoring system according to Claim 1,

wherein said system includes a probe, which detects at least one of electron current, electron energy distribution, ion current, electron temperature, electron density, and charge storage amount, as said sensor.

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